

IN THE CLAIMS

Please amend the claims to read as follows:

Listing of Claims

1-10. (Canceled).

11. (Previously presented) A resin molded type semiconductor device comprising: a semiconductor chip which is mounted on a die pad of a lead frame; thin metal wires which electrically connect terminals of an upper face of said semiconductor chip to inner lead portions of said lead frame; a sealing resin which seals an outer peripheral region of said semiconductor chip, said region including a thin metal wire region of the upper face of said semiconductor chip; and outer lead portions which are arranged in a bottom face region of said sealing resin and which are formed to be continuous to respective inner lead portions, wherein at least one groove portion is formed in a surface of each of said inner lead portions, a connecting portion of each of said thin metal wires is coupled to a respective inner lead portion at a flat surface region of said respective inner lead portion adjacent said at least one groove portion.

12. (Previously presented) A resin molded type semiconductor device according to claim 11, wherein exposed faces of said outer lead portion are arranged in a same level as an outer face of said sealing resin.

13. (Previously presented) A resin molded type semiconductor device comprising:

a semiconductor chip which is mounted on a die pad of a lead frame;

thin metal wires which electrically connect terminals of an upper face of said semiconductor chip to inner lead portions of said lead frame;

a sealing resin which seals an outer peripheral region of said semiconductor chip and which contacts a bottom face of said semiconductor chip, said region including a thin metal wire region of the upper face of said semiconductor chip; and

outer lead portions which are arranged in a bottom face region of said sealing resin and which are formed to be continuous to respective inner lead portions.

14. (New) A resin molded type semiconductor device comprising:

a die pad; and

leads including inner lead portions and outer lead portions, each of said inner lead portions including at least one groove portion which is formed in a surface thereof;

a semiconductor chip mounted over said die pad;

thin metal wires which electrically connect terminals of said semiconductor chip to said inner lead portions at a position not on top of said groove portion; and

a sealing resin which seals said groove portion, an outer peripheral region of said semiconductor chip and an entire upper region of said inner lead portions, said outer peripheral region including a region of said thin metal wires,

wherein said sealing resin leaves an entire bottom surface of said inner lead portions unsealed.

15. (New) The resin molded type semiconductor device according to claim 14, wherein each of said inner lead portions includes said at least one groove portion which is formed in an upper surface of said inner lead portions.

16. (New) The resin molded type semiconductor device according to claim 15, wherein said die pad is disposed higher than said upper surface of said inner lead portions, and said sealing resin seals a lower region of said die pad.

17. (New) The resin molded type semiconductor device according to claim 16, wherein a bottom surface of said die pad is disposed higher than a bottom surface of said inner lead portions.

18. (New) The resin molded type semiconductor device according to claim 17, wherein at least a portion of said outer periphery of said semiconductor chip extends outward from said outer periphery of said die pad.

19. (New) The resin molded type semiconductor device according to claim 18, wherein said groove portion absorbs stress at a connection between said thin metal wires and said inner lead portions.

20. (New) A resin molded type semiconductor device according to claim 19, wherein a total thickness is not greater than a sum of a thickness of said semiconductor chip and 1 mm.

21. (New) The resin molded type semiconductor device according to claim 19, wherein exposed faces of said outer lead portions are substantially arranged in a same plane as an outer surface of said sealing resin.

22. (New) A resin molded type semiconductor device comprising:

a die pad; and

leads each including at least one groove portion which is formed in a surface thereof;

a semiconductor chip mounted over said die pad;

thin metal wires which electrically connect terminals of said semiconductor chip to said leads at a position not on top of said groove portion; and

a sealing resin which seals said groove portion, said thin metal wires, said semiconductor chip and an upper region of said leads,

wherein said sealing resin leaves an entire bottom surface of said leads unsealed.

23. (New) The resin molded type semiconductor device according to claim 22, wherein each of said leads includes said at least one groove portion which is formed in an upper surface.

of said leads.

24. (New) The resin molded type semiconductor device according to claim 23, wherein said die pad is disposed higher than said upper surface of said leads.

25. (New) The resin molded type semiconductor device according to claim 24, wherein a bottom surface of said die pad is disposed higher than a bottom surface of said leads.

26. (New) The resin molded type semiconductor device according to claim 25, wherein at least a portion of said outer periphery of said semiconductor chip extends outward from said outer periphery of said die pad.

27. (New) The resin molded type semiconductor device according to claim 26, wherein said groove portion absorbs stress at a connection between said thin metal wires and said leads.

28. (New) A resin molded type semiconductor device according to claim 27, wherein a total thickness is not greater than a sum of a thickness of said semiconductor chip and 1 mm.

29. (New) The resin molded type semiconductor device according to claim 19, wherein exposed faces of said leads are substantially arranged in a same plane as an outer surface of said sealing resin.